

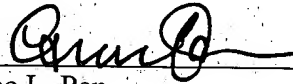
Any additionally required fee or overpayment in any fee occasioned by this paper may be charged or credited to Deposit Account No. 50-0320.

Applicants submit that the presented claims are in allowable form, and early and favorable consideration is earnestly requested.

Respectfully submitted,

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

In the Claims:

Please amend claim 1 by rewriting the same as follows:

--1. (Amended) A semiconductor device comprising:

a semiconductor substrate; and

a gate insulating film provided on said semiconductor substrate, at least a part of
[which includes] said gate insulating film including an insulating film containing metal, silicon
and oxygen;

wherein at least one of fluorine and nitrogen is contained in said insulating film
containing metal, silicon and oxygen.--